ALPHA & OMEGA SEMICONDUCTOR, LTD.

Rev 0: Dec 2003
Rev 1: Mar 2004

AOD442, AOD442L (Lead-Free)
N-Channel Enhancement Mode Field Effect Transistor

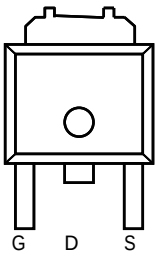
General Description

The AOD442 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. This device is suitable for use as a load switch or in PWM applications. AOD442L is offered in a lead-free package.

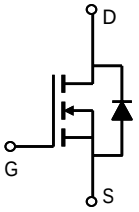
Features

V_{DS} (V) = 60V
I_D = 38A
$R_{DS(ON)}$ < 20mΩ (V_{GS} = 10V)
$R_{DS(ON)}$ < 25mΩ (V_{GS} = 4.5V)

TO-252
D-PAK



Top View
Drain Connected to Tab



Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current [B,G]	T_C=25°C [G]	I_D	38	A
	T_C=100°C [B]		27	
Pulsed Drain Current		I_{DM}	60	
Avalanche Current [C]		I_{AR}	30	A
Repetitive avalanche energy L=0.1mH [C]		E_{AR}	140	mJ
Power Dissipation [B]	T_C=25°C	P_D	60	W
	T_C=100°C		30	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 175	°C

Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	17.4	25	°C/W
Maximum Junction-to-Ambient [A]	Steady-State		51	60	°C/W
Maximum Junction-to-Lead [C]	Steady-State	$R_{\theta JL}$	1.8	2.5	°C/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250µA, V_{GS}=0V	60			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=48V, V_{GS}=0V			1	µA
		T_J=55°C			5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}= ±20V			100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} I_D=250µA	1	2.1	3	V
$I_{D(ON)}$	On state drain current	V_{GS}=10V, V_{DS}=5V	60			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=20A		16	20	mΩ
		T_J=125°C		31		
		V_{GS}=4.5V, I_D=20A		20	25	mΩ
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=20A	4.5	5.6		S
V_{SD}	Diode Forward Voltage	I_S=1A,V_{GS}=0V		0.74	1	V
I_S	Maximum Body-Diode Continuous Current				4	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=30V, f=1MHz		1920	2300	pF
C_{oss}	Output Capacitance			155		pF
C_{rss}	Reverse Transfer Capacitance			116		pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz		0.65	0.8	Ω
SWITCHING PARAMETERS						
Q_g(10V)	Total Gate Charge	V_{GS}=10V, V_{DS}=30V, I_D=20A		47.6	68	nC
Q_g(4.5V)	Total Gate Charge			24.2	30	nC
Q_{gs}	Gate Source Charge			6		nC
Q_{gd}	Gate Drain Charge			14.4		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=30V, R_L=1.5Ω, R_{GEN}=3Ω		7.4		ns
t_r	Turn-On Rise Time			5.1		ns
$t_{D(off)}$	Turn-Off DelayTime			28.2		ns
t_f	Turn-Off Fall Time			5.5		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=20A, dI/dt=100A/µs		34	41	ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=20A, dI/dt=100A/µs		46		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The Power dissipation P_{DSM} is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C. The value in any a given application depends on the user's specific board design, and the maximum temperature fo 175°C may be used if the PCB allows it.

B. The power dissipation P_D is based on $T_{J(MAX)}$=175°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C: Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=175°C.

D. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to case $R_{\theta JC}$ and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300µs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedence which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=175°C.

G. The maximum current rating is limited by bond-wires.

H. These tests are performed with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

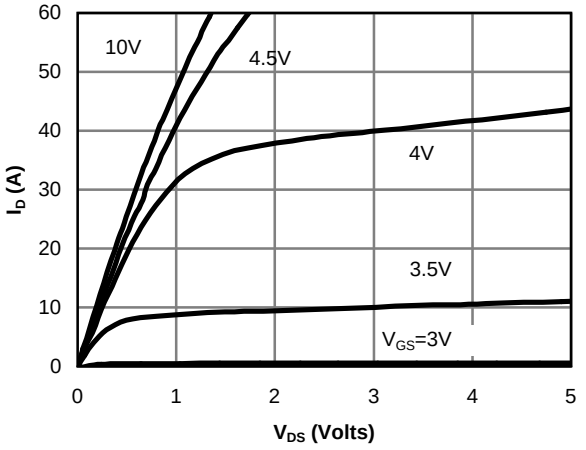


Fig 1: On-Region Characteristics

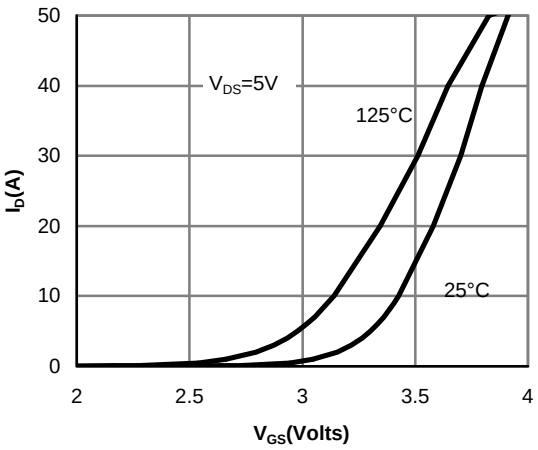


Figure 2: Transfer Characteristics

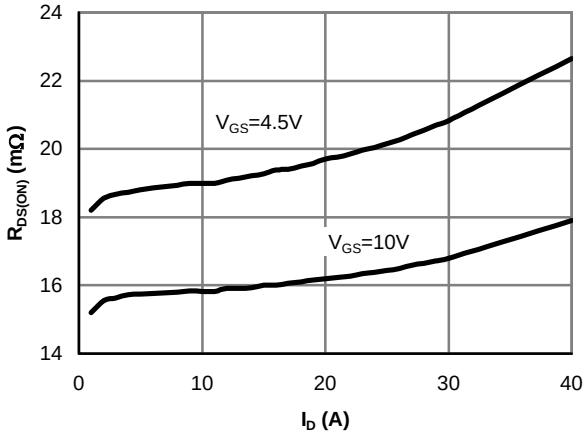


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

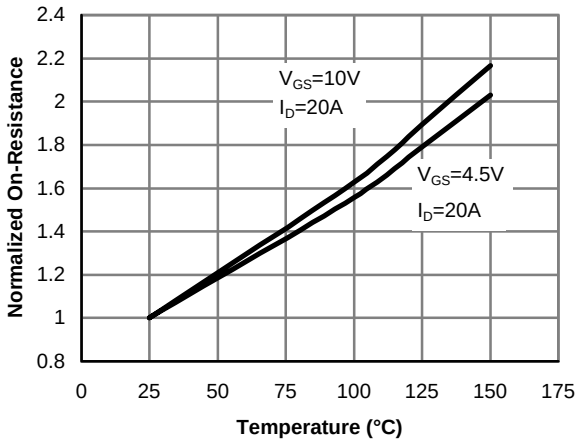


Figure 4: On-Resistance vs. Junction Temperature

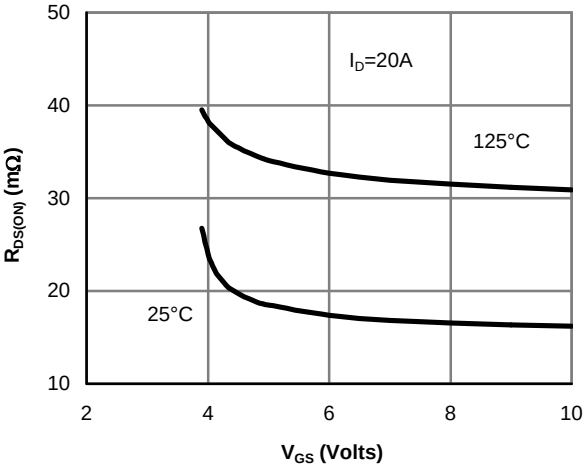


Figure 5: On-Resistance vs. Gate-Source Voltage

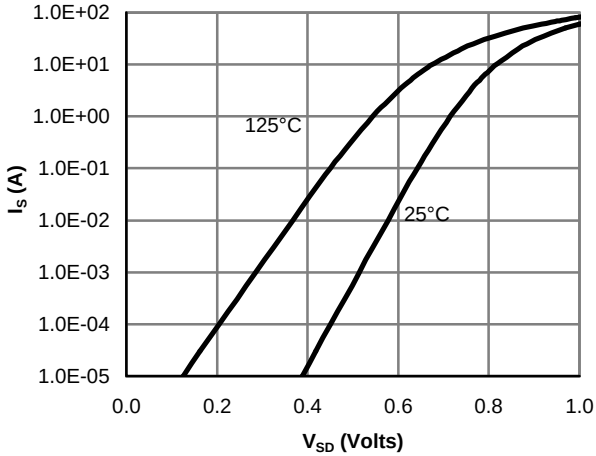


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

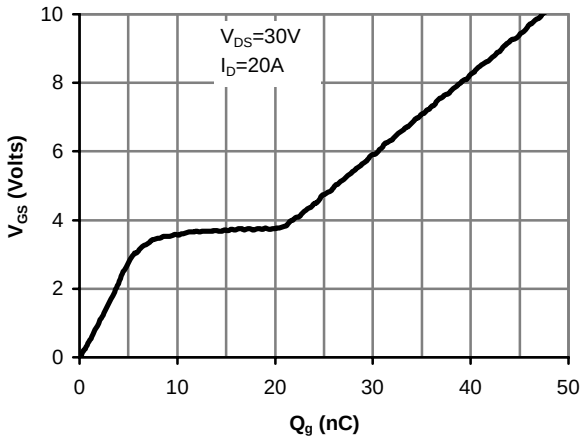


Figure 7: Gate-Charge Characteristics

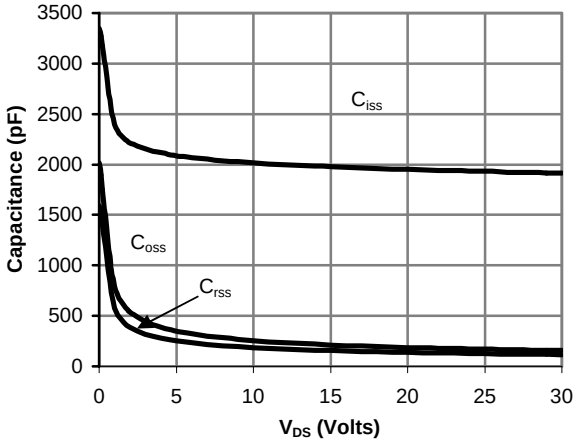


Figure 8: Capacitance Characteristics

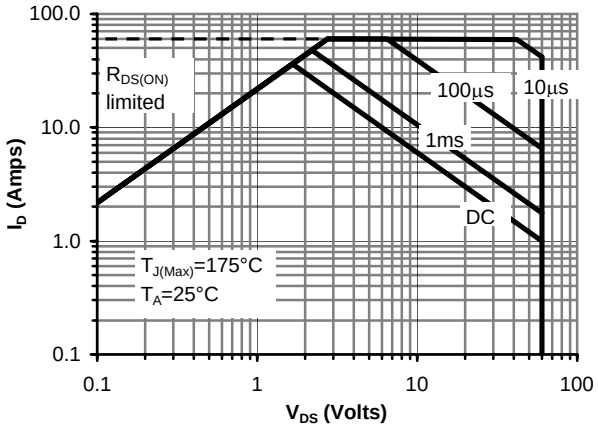


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

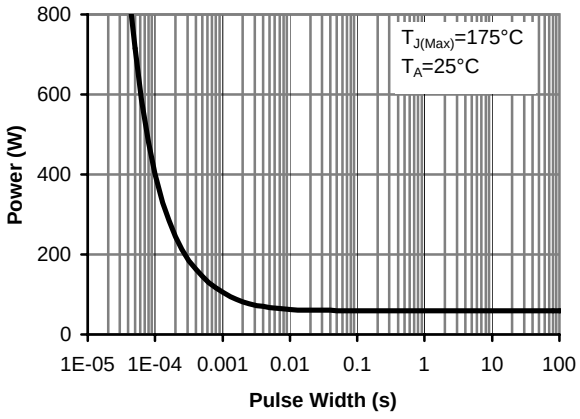


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

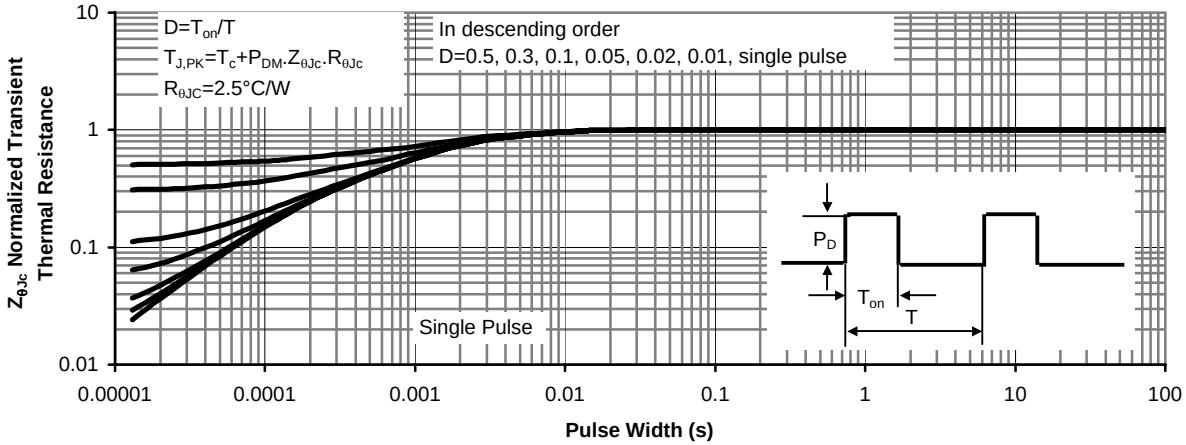


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

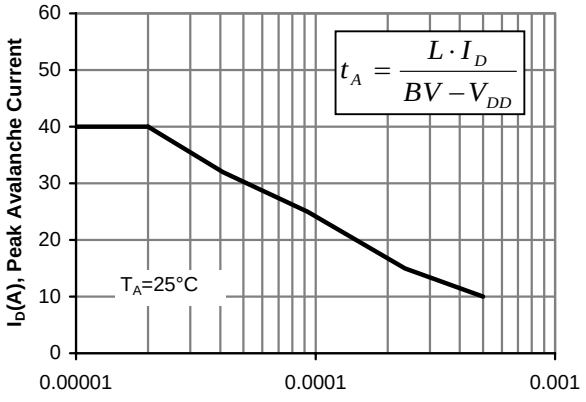


Figure 12: Single Pulse Avalanche capability

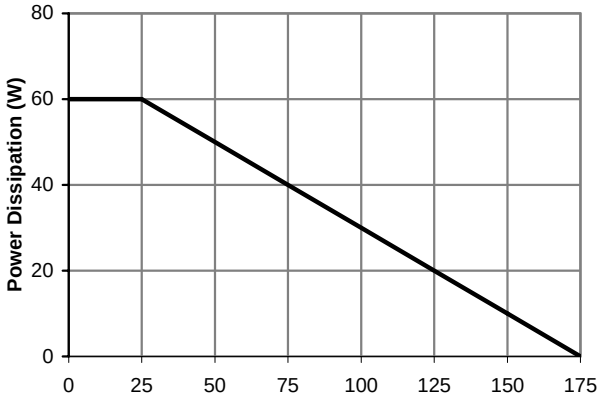


Figure 13: Power De-rating (Note B)

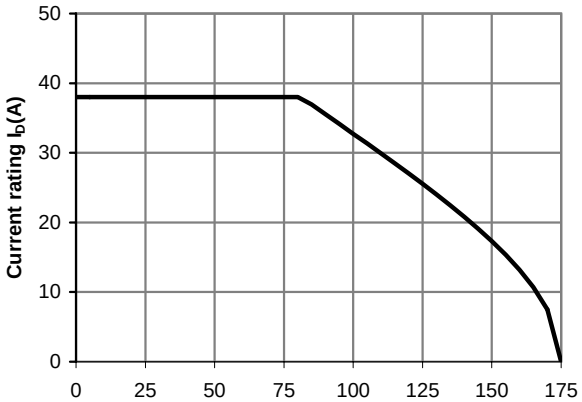


Figure 14: Current De-rating (Note B)

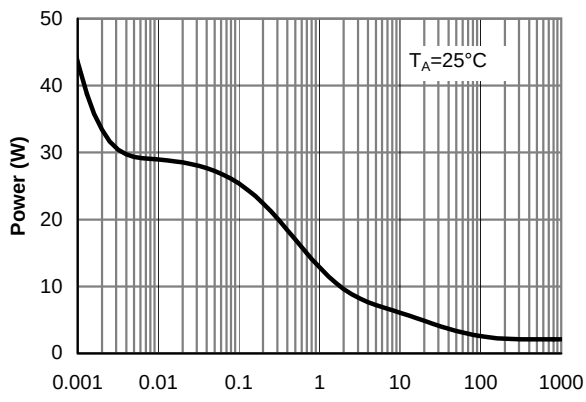


Figure 15: Single Pulse Power Rating Junction-to-Ambient (Note H)

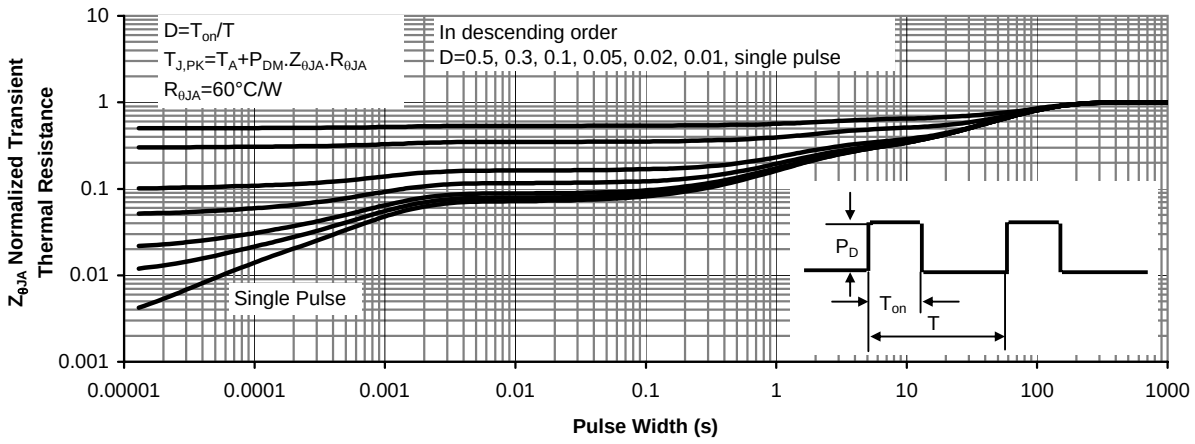
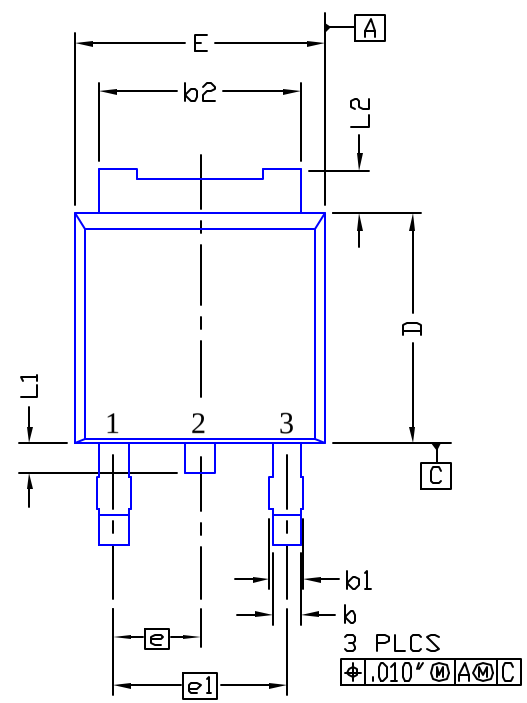
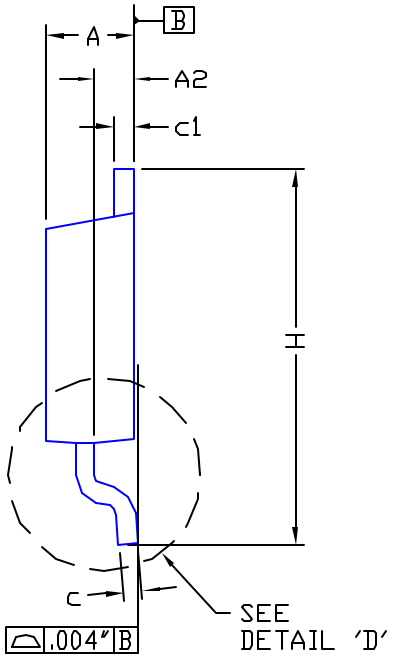
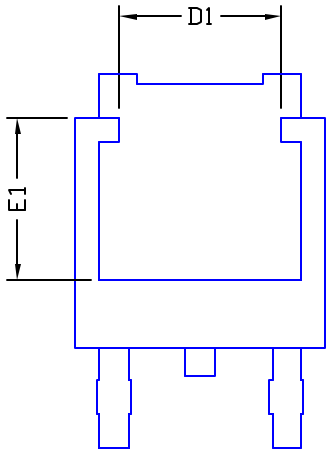


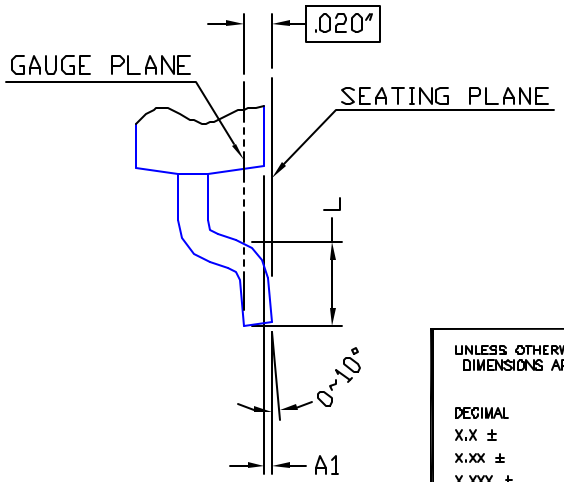
Figure 16: Normalized Maximum Transient Thermal Impedance (Note H)

REVISION HISTORY				
REV	DESCRIPTION	DATE	ORIGINATED	RELEASED
A	INITIAL RELEASE.	7/29/02	L. LUO	L. LUO









DETAIL 'D'
SCALE: 1.5X

NOTE
1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS
2. DIMENSION L IS MEASURED IN GAGE PLANE
3. TOLERANCE 0.10 mm UNLESS OTHERWISE SPECIFIED
4. CONTROLLING DIMENSION IS MILLIMETER. CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.
5. FOLLOWED FROM JEDEC TO-252 (AA)

SYMBOL	DIMENSION IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	2.235	2.286	2.388	0.088	0.090	0.094
A1	0.000	-----	0.102	0.000	-----	0.004
A2	0.889	-----	1.143	0.035	-----	0.045
b	0.686	0.762	0.889	0.027	0.030	0.035
b1	0.889	-----	1.143	0.035	-----	0.045
b2	5.207	4.45	5.461	0.205	-----	0.215
c	0.457	0.508	0.559	0.018	0.020	0.022
c1	0.483	-----	0.584	0.019	-----	0.023
D	5.969	6.096	6.223	0.235	0.240	0.245
D1	4.318	-----	5.334	0.170	-----	0.210
E	6.477	6.604	6.731	0.255	0.260	0.265
E1	4.318	-----	-----	0.170	-----	-----
e	2.286 BSC.			0.090 BSC.		
e1	4.572 BSC.			0.180 BSC.		
H	9.779	-----	10.414	0.385	-----	0.410
L	1.270	-----	2.032	0.050	-----	0.080
L1	0.635	-----	1.016	0.025	-----	0.040
L2	0.889	-----	1.270	0.035	-----	0.050

UNLESS OTHERWISE SPECIFIED DIMENSIONS ARE IN INCHES

DECIMAL: X.X ±, X.XX ±, X.XXX ±
ANGULAR: ±

INTERPRET DIM AND TOL PER ASME Y14.5M – 1994

PRINTING IS SCALED TO FIT DO NOT SCALE DRAWING

THIRD ANGLE PROJECTION

APPROVALS	DATE
DESIGN L. LUO	7/29/02
CHECKED L. LUO	7/29/02
APPROVED Y. HO	7/29/02

ALPHA & OMEGA SEMICONDUCTOR, INC.

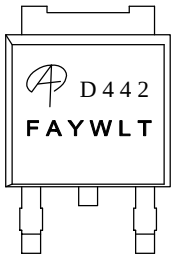
TITLE: DPAK (TO-252 AA) CASE OUTLINE DRAWING

SCALE	DWG NUMBER	SHEET	REV
NTS	PO-00009	1 OF 1	A

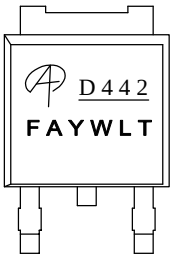
Document No.	PD-00256
Version	rev B
Title	AOD442 Marking Description

ALPHA & OMEGA
SEMICONDUCTOR, LTD.

DPAK PACKAGE MARKING DESCRIPTION



Standard product



Green product

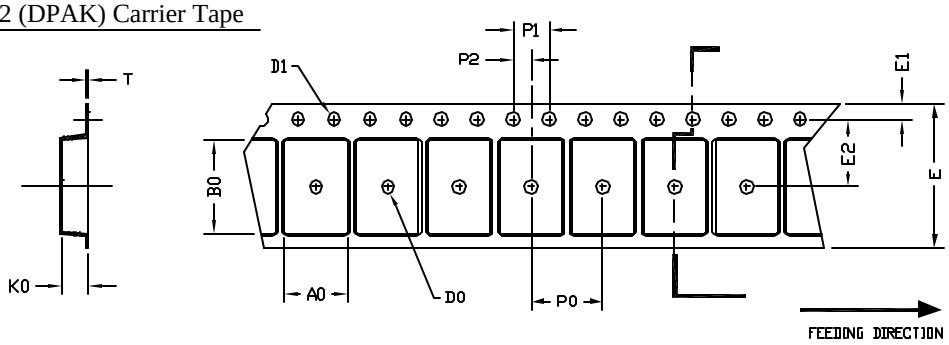
NOTE:
LOGO - AOS LOGO
D442 - PART NUMBER CODE.
F&A - FOUNDRY AND ASSEMBLY LOCATION
Y - YEAR CODE
W - WEEK CODE.
L T - ASSEMBLY LOT CODE

PART NO.	DESCRIPTION	CODE
AOD442	Standard product	D442
AOD442L	Green product	D442

ALPHA & OMEGA
SEMICONDUCTOR, LTD.

TO-252 (DPAK)
Tape and Reel Data

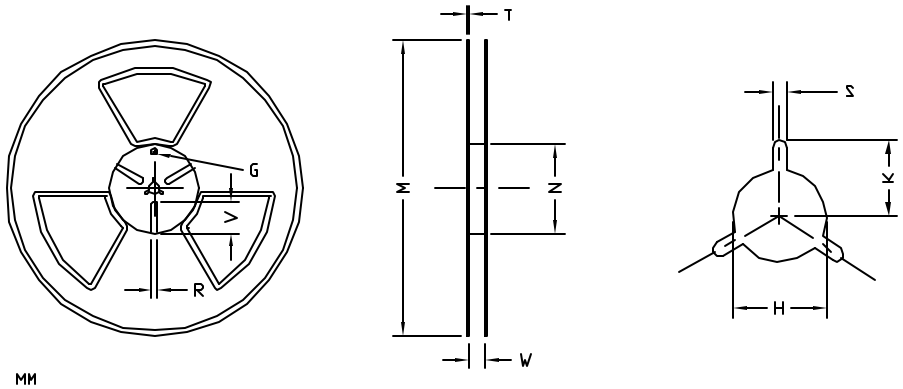
TO-252 (DPAK) Carrier Tape



UNIT: MM

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
TO-252(DPAK) (16 mm)	6.90 ±0.10	10.50 ±0.10	2.70 ±0.10	1.50 ±0.10	1.50 MIN.	16.00 ±0.10	1.75 ±0.10	7.50 ±0.10	8.00 ±0.10	4.00 ±0.10	2.00 ±0.10	0.30 ±0.05

TO-252 (DPAK) Reel



UNIT: MM

TAPE SIZE	REEL SIZE	M	N	W	T	H	K	S	G	R	V
16 mm	ø330	ø330.00 ±0.10	ø99.50 ±0.10	17.50 ±0.50	2.30	ø13.50 ±0.10	10.60	2.50 ±0.10	---	---	---

TO-252 (DPAK)

Leader / Trailer & Orientation